



No.1637B

2SC3638

NPN Triple Diffused Planar Silicon Transistor
VERY HIGH-DEFINITION DISPLAY
HORIZONTAL DEFLECTION OUTPUT APPLICATIONS

Features

- . High reliability (Adoption of HVP process)
- . Fast speed.
- . High breakdown voltage.
- . Adoption of MBIT process.

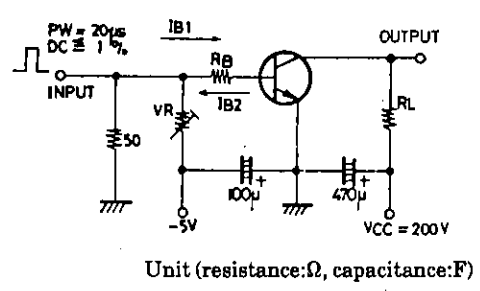
Absolute Maximum Ratings at Ta=25°C

			unit
Collector-to-Base Voltage	V _{CB0}	900	V
Collector-to-Emitter Voltage	V _{CE0}	500	V
Emitter-to-Base Voltage	V _{EB0}	7	V
Collector Current	I _C	15	A
Peak Collector Current	i _{cp}	25	A
Collector Dissipation	P _C	100	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

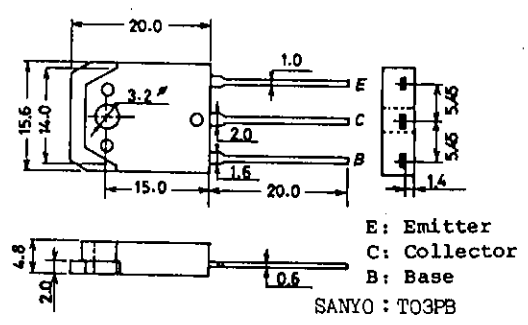
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =500V, I _E =0			10	µA
	I _{CES}	V _{CE} =900V, R _{BE} =0			0.5	mA
Collector-to-Emitter Sustain Voltage	V _{CEO(sus)}	I _C =100mA, I _B =0	500			V
Emitter Cutoff Current	I _{EB0}	V _{EB} =5V, I _C =0			1	mA
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =7A, I _B =1.4A			2	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =7A, I _B =1.4A			1.5	V
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =1.4A	8			
Storage Time	t _{stg}	I _C =7A, I _{B1} =1.4A, I _{B2} =-2.8A			3.0	µs
Fall Time	t _f	I _C =7A, I _{B1} =1.4A, I _{B2} =-2.8A		0.1	0.2	µs

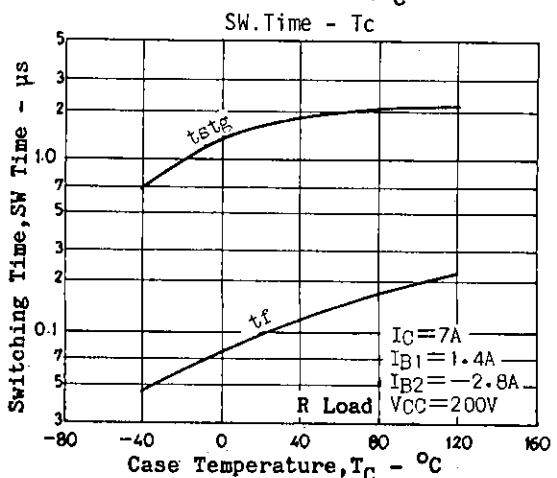
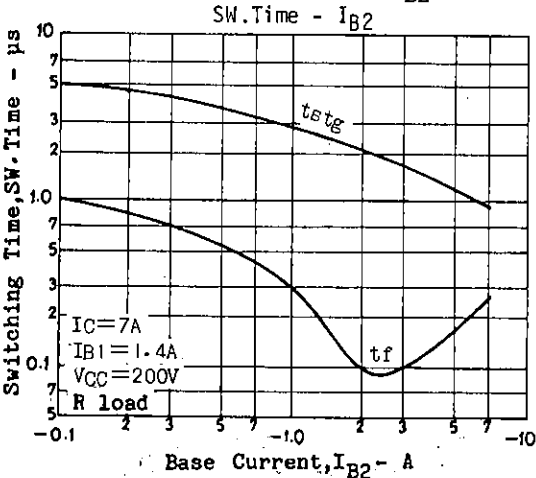
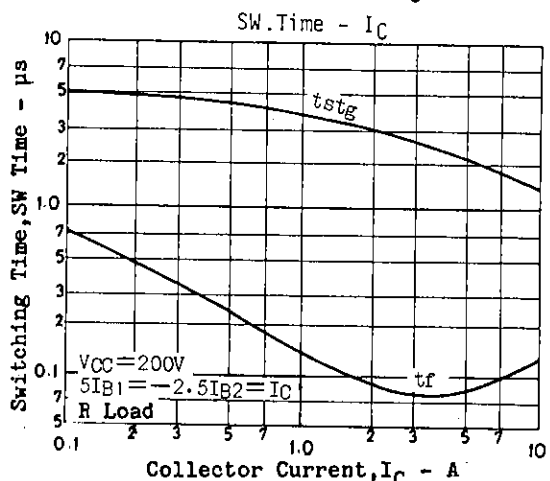
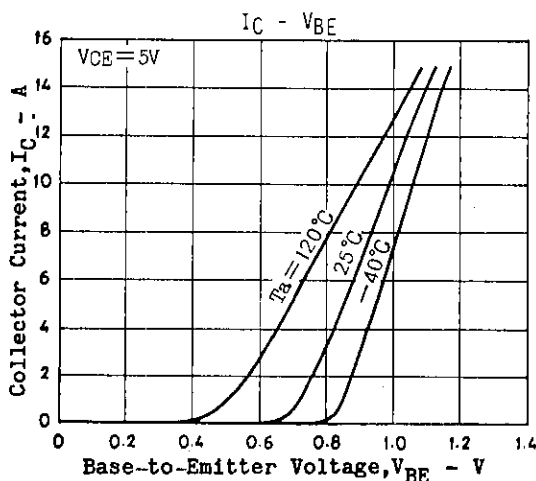
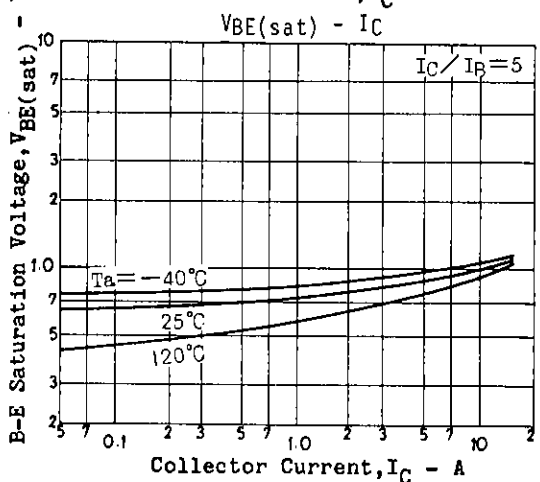
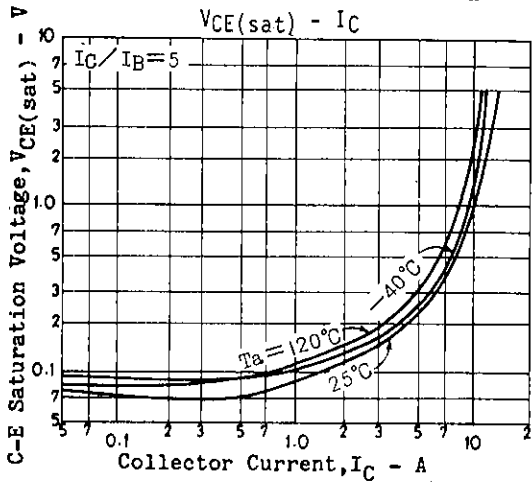
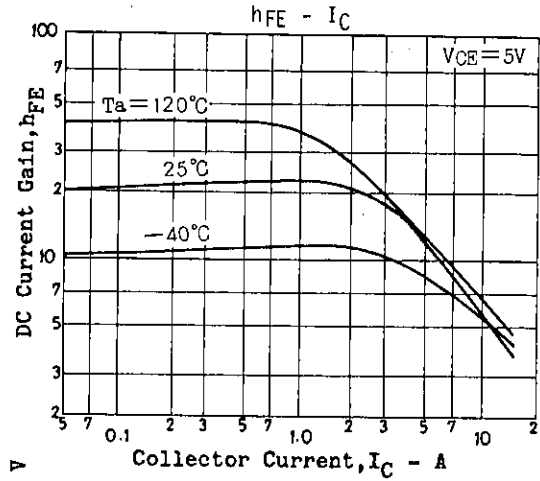
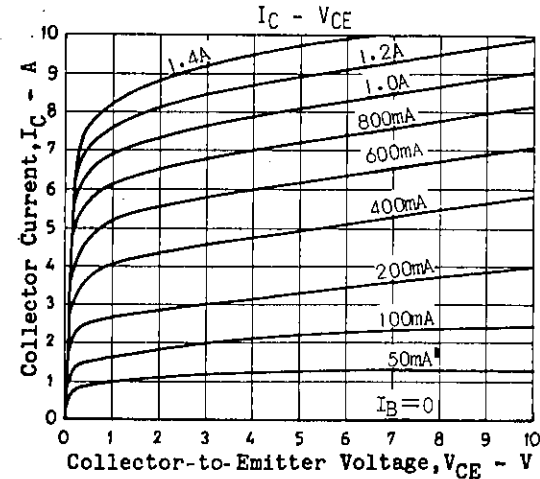
Switching Time Test Circuit

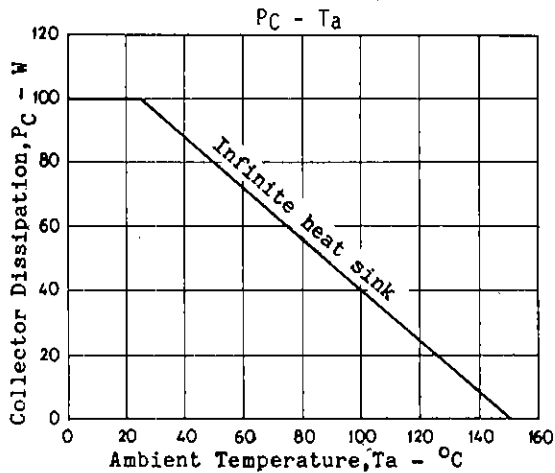
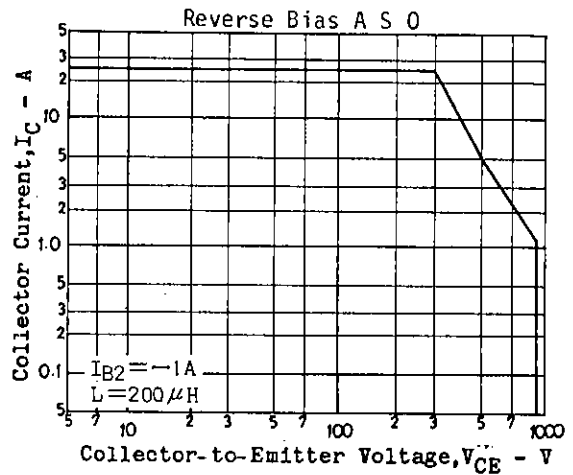
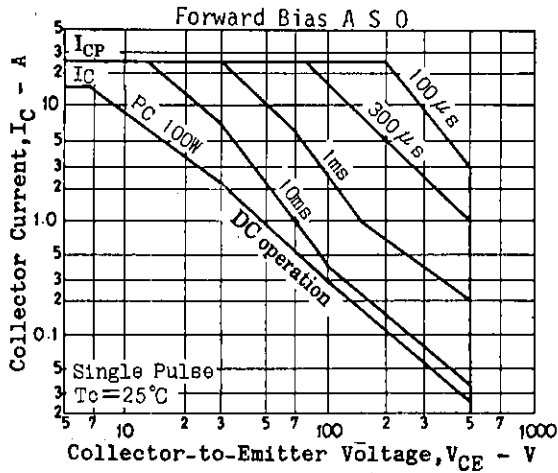


Package Dimensions 2022 (unit: mm)



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